## 1 Scope

The present specifications shall apply to a RH1C.

## 2 Outline

Туре	Silicon Diode			
Structure	Resin Molded Flammability:UL94-V0(Equivalent)			
Applications	High Frequency Rectification, etc.			

## 3 Absolute maximum ratings

B Abso	olute maximum ratings	Ś			
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V <sub>RSM</sub>	V	1000	
2	Peak Reverse Voltage	V <sub>RM</sub>	V	1000	
3	Average Forward Current	$I_{F(AV)}$	А	0.6	Refer to derating curve in Section 6
4	Peak Surge Forward Current	I <sub>FSM</sub>	А	35	10ms. Half sine wave, one shot
5	I <sup>2</sup> t Limiting Value	I <sup>2</sup> t	A <sup>2</sup> s	6.125	$1 \text{ ms} \leq t \leq 10 \text{ ms}$
6	Junction Temperature	Tj	°C	-40 to +150	
7	Storage Temperature	T <sub>stg</sub>	°C	-40 to +150	

## 4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	ymbol	Unit	Value	Conditions
1	Forward Voltage Drop	$\mathbf{V}_{\mathrm{F}}$	V	1.3 max.	I <sub>F</sub> =0.6A
2	2 Reverse Leakage Current		μΑ	5 max.	V <sub>R</sub> =V <sub>RM</sub>
3	Reverse Leakage Current Under High Temperature	H•I <sub>R</sub>	μΑ	70 max.	$V_R=V_{RM}, T_a=100^{\circ}C$
4	4 Reverse Recovery Time		μs	4.0 max.	I <sub>F</sub> =I <sub>RP</sub> =10mA 90% Recovery point, T <sub>j</sub> =25°C
	Reverse Recovery Time	Trr-2	μs	1.3 max.	I <sub>F</sub> =100mA, I <sub>R</sub> =200mA 75% Recovery point ,T <sub>j</sub> =25°C
5	Thermal Resistance	Rth (j-l)	°C /W	15 max.	Between Junction and Lead



